

# RF MOSFET Power Transistor, 80W, 28V

## 2 - 175 MHz

### DU2880V

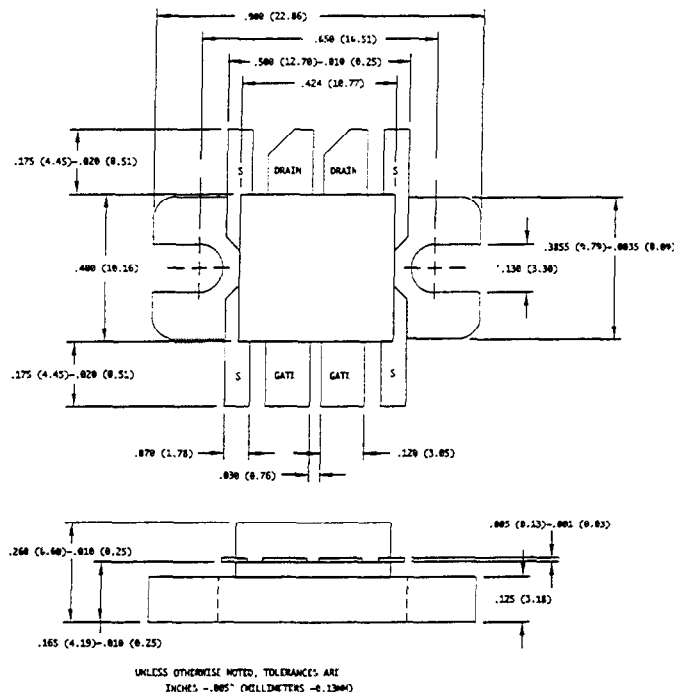
V2.00

#### Features

- N-Channel Enhancement Mode Device
- DMOS Structure
- Lower Capacitances for Broadband Operation
- High Saturated Output Power
- Lower Noise Figure Than Competitive Devices

#### Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	65	V
Gate-Source Voltage	$V_{GS}$	20	V
Drain-Source Current	$I_{DS}$	8*	A
Power Dissipation	$P_D$	206	W
Junction Temperature	$T_J$	200	°C
Storage Temperature	$T_{STG}$	-55 to +150	°C
Thermal Resistance	$\theta_{JC}$	0.85	°C/W



#### Electrical Characteristics at 25°C

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	$BV_{DSS}$	65	-	V	$V_{GS}=0.0\text{ V}$ , $I_{DS}=10.0\text{ mA}^*$
Drain-Source Leakage Current	$I_{DSS}$	-	2.0	mA	$V_{DS}=28.0\text{ V}$ , $V_{GS}=0.0\text{ V}^*$
Gate-Source Leakage Current	$I_{GSS}$	-	2.0	$\mu\text{A}$	$V_{GS}=20.0\text{ V}$ , $V_{DS}=0.0\text{ V}^*$
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	V	$V_{DS}=10.0\text{ V}$ , $I_{DS}=200.0\text{ mA}^*$
Forward Transconductance	$G_M$	1.0	-	S	$V_{DS}=10.0\text{ V}$ , $I_{DS}=2000.0\text{ mA}$ , $\Delta V_{GS}=1.0\text{ V}$ , 80 $\mu\text{s}$ Pulse*
Input Capacitance	$C_{ISS}$	-	90	pF	$V_{DS}=28.0\text{ V}$ , $F=1.0\text{ MHz}^*$
Output Capacitance	$C_{OSS}$	-	80	pF	$V_{DS}=28.0\text{ V}$ , $F=1.0\text{ MHz}^*$
Reverse Capacitance	$C_{RSS}$	-	16	pF	$V_{DS}=28.0\text{ V}$ , $F=1.0\text{ MHz}^*$
Power Gain	$G_p$	13	-	dB	$V_{DD}=28.0\text{ V}$ , $I_{DC}=400\text{ mA}$ , $P_{OUT}=80.0\text{ W}$ , $F=175\text{ MHz}$
Drain Efficiency	$\eta_D$	60	-	%	$V_{DD}=28.0\text{ V}$ , $I_{DC}=400\text{ mA}$ , $P_{OUT}=80.0\text{ W}$ , $F=175\text{ MHz}$
Load Mismatch Tolerance	VSWR-T	-	30:1	-	$V_{DD}=28.0\text{ V}$ , $I_{DC}=400\text{ mA}$ , $P_{OUT}=80.0\text{ W}$ , $F=175\text{ MHz}$

\* Per Side

Specifications Subject to Change Without Notice.

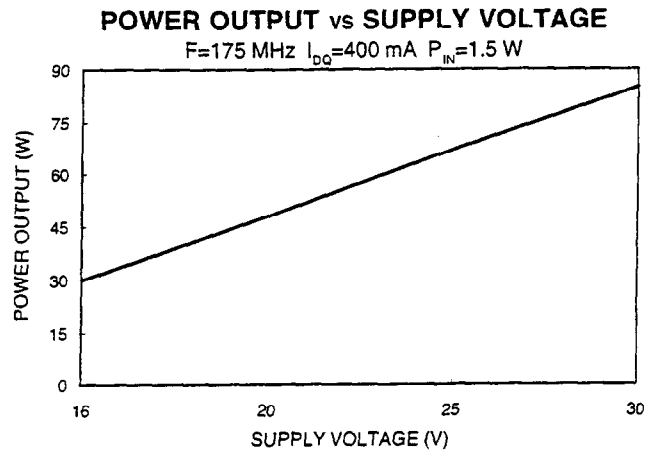
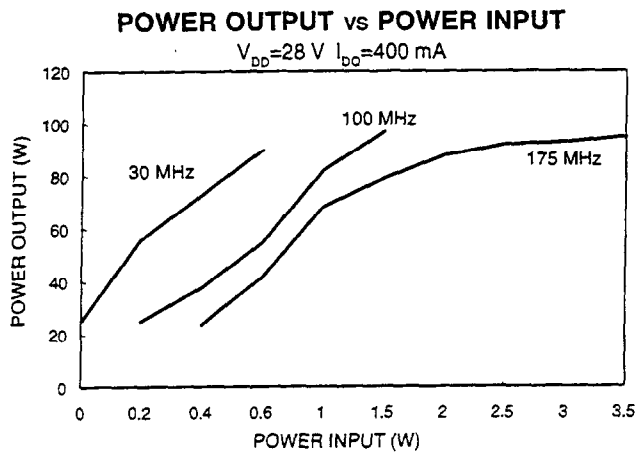
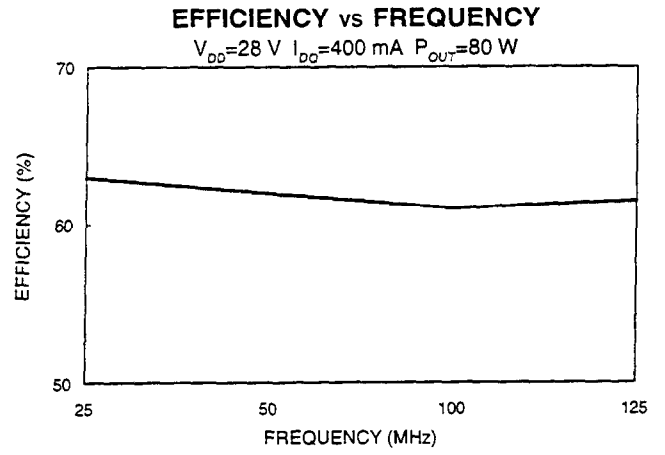
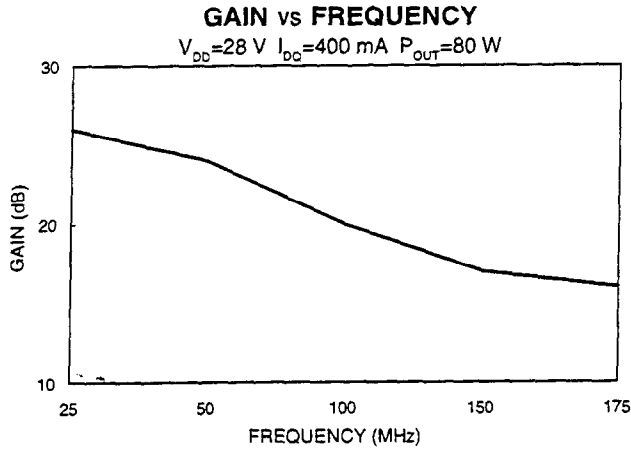
M/A-COM, Inc.

North America: Tel. (800) 366-2266  
Fax (800) 618-8883

Asia/Pacific: Tel. +81 (03) 3226-1671  
Fax +81 (03) 3226-1451

Europe: Tel. +44 (1344) 869 595  
Fax +44 (1344) 300 020

Typical Broadband Performance Curves



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Typical Device Impedance

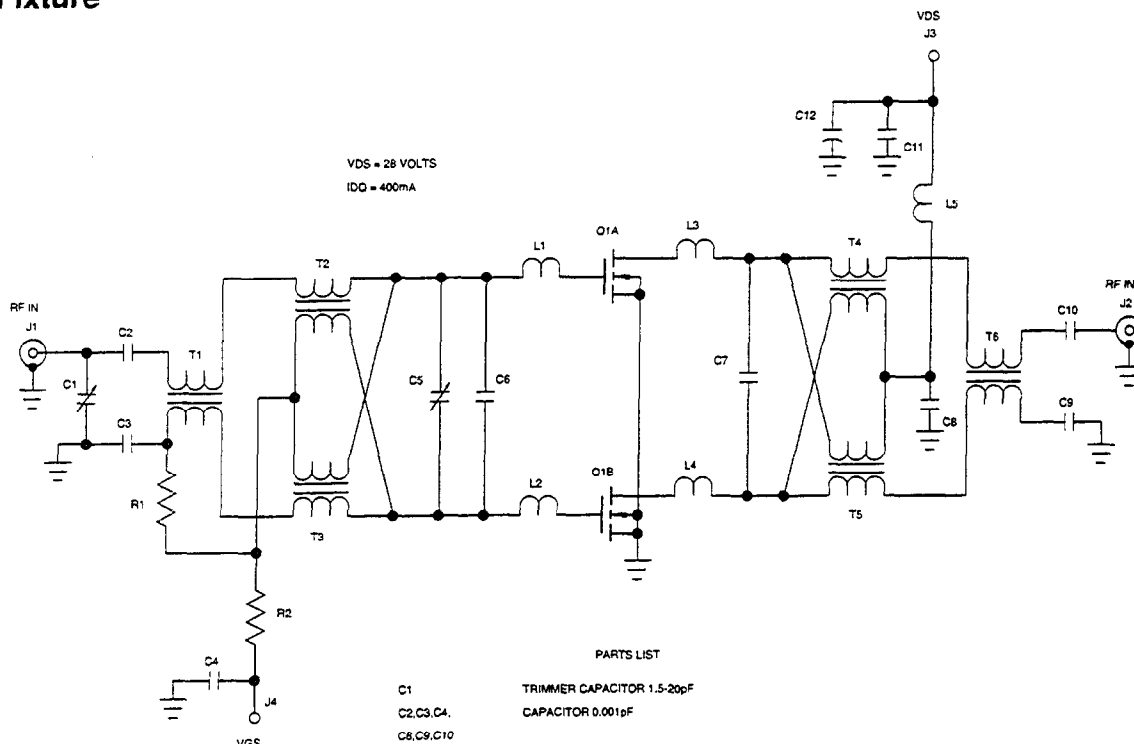
Frequency (MHz)	Z <sub>IN</sub> (OHMS)	Z <sub>LOAD</sub> (OHMS)
30	4.5 - j 14.5	13.5 + j 4.5
100	3.0 - j 10.5	13.5 + j 6.0
175	2.0 - j 7.5	12.0 + j 4.5

V<sub>DD</sub>=28 V, I<sub>DD</sub>=400 mA, P<sub>OUT</sub>=80 Watts

Z<sub>IN</sub> is the series equivalent input impedance of the device from gate to gate.

Z<sub>LOAD</sub> is the optimum series equivalent load impedance as measured from drain to drain.

RF Test Fixture



PARTS LIST

- C1 TRIMMER CAPACITOR 1.5-20pF
- C2,C3,C4, CAPACITOR 0.001pF
- C5,C6,C9,C10
- C5 TRIMMER CAPACITOR 5-80pF
- C6 CAPACITOR 68pF
- C7 CAPACITOR 50pF
- C12 ELECTROLYTIC CAPACITOR 100µF 50 VOLTS
- L1,L2 0.50" X 0.10" TRACE ON BOARD - Ø0.125" X Ø0.25" LOOP
- L3,L4 0.87" X 0.10" TRACE ON BOARD
- L5 7.5 TURNS OF NO. 20 AWG COPPER WIRE X Ø0.31"
- R1 RESISTOR 18 OHMS 2 WATTS
- R2 RESISTOR 10K OHMS
- T1,T6 50 OHM BALUN CORES, 2 TURNS OF 50 OHM COAX THRU 2 STACKPOLE 57-1522
- T2,T3,T4 4:1 TRANSFORMER 1 TURN OF 2 50 OHM COAX IN
- T5 PARALLEL THRU 2 STACKPOLE 57-1522 BALUN CORES
- Q1 DU2880V
- BOARD FRA 0.062"

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